
HM62W8511HC Series

4M High Speed SRAM (512-kword $\times$ 8-bit)

HITACHI

ADE-203-1201 (Z)
Preliminary
Rev. 0.0
Sep. 20, 2000

Description

The HM62W8511HC is a 4-Mbit high speed static RAM organized 512-kword $\times$ 8-bit. It has realized high speed access time by employing CMOS process (6-transistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The HM62W8511HC is packaged in 400-mil 36-pin SOJ for high density surface mounting.

Features

- Single supply : 3.3 V $\pm$ 0.3 V
- Access time : 10 ns (max)
- Completely static memory
 - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
 - All inputs and outputs
- Operating current : 115 mA (max)
- TTL standby current : 40 mA (max)
- CMOS standby current : 5 mA (max)
 - : 1 mA (max) (L-version)
- Data retention current : 0.6 mA (max) (L-version)
- Data retention voltage : 2 V (min) (L-version)
- Center V_{CC} and V_{SS} type pinout

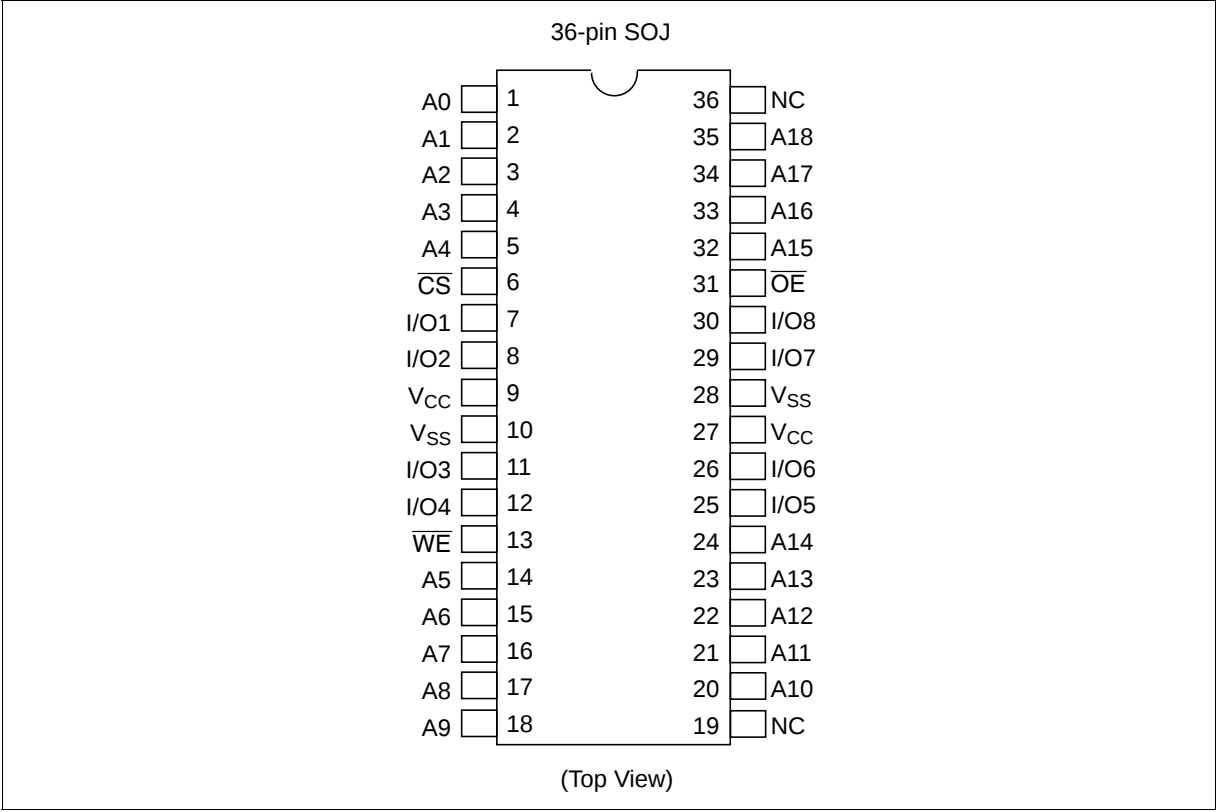
Preliminary: The specification of this device are subject to change without notice. Please contact your nearest Hitachi's Sales Dept. regarding specification.

HM62W8511HC Series

Ordering Information

Type No.	Access time	Package
HM62W8511HCJP-10	10 ns	400-mil 36-pin plastic SOJ (CP-36D)
HM62W8511HCLJP-10	10 ns	

Pin Arrangement



Pin Description

Pin name	Function
A0 to A18	Address input
I/O1 to I/O8	Data input/output
CS	Chip select
OE	Output enable
WE	Write enable
V _{cc}	Power supply
V _{ss}	Ground
NC	No connection

Operation Table

$\overline{\text{CS}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	Mode	V_{CC} current	I/O	Ref. cycle
H	×	×	Standby	$I_{\text{SB}}, I_{\text{SB1}}$	High-Z	—
L	H	H	Output disable	I_{CC}	High-Z	—
L	L	H	Read	I_{CC}	Dout	Read cycle (1) to (3)
L	H	L	Write	I_{CC}	Din	Write cycle (1)
L	L	L	Write	I_{CC}	Din	Write cycle (2)

Note: ×: H or L

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	−0.5 to +4.6	V
Voltage on any pin relative to V_{SS}	V_{T}	−0.5* ¹ to $V_{\text{CC}}+0.5^{*2}$	V
Power dissipation	P_{T}	1.0	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	−55 to +125	°C
Storage temperature under bias	T_{bias}	−10 to +85	°C

Notes: 1. V_{T} (min) = −2.0 V for pulse width (under shoot) ≤ 6 ns.
2. V_{T} (max) = $V_{\text{CC}}+2.0$ V for pulse width (over shoot) ≤ 6 ns.

Recommended DC Operating Conditions (T_{a} = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}^{*3}	3.0	3.3	3.6	V
	V_{SS}^{*4}	0	0	0	V
Input voltage	V_{IH}	2.0	—	$V_{\text{CC}} + 0.5^{*2}$	V
	V_{IL}	−0.5* ¹	—	0.8	V

Notes: 1. V_{IL} (min) = −2.0 V for pulse width (under shoot) ≤ 6 ns.
2. V_{IH} (max) = $V_{\text{CC}}+2.0$ V for pulse width (over shoot) ≤ 6 ns.
3. The supply voltage with all V_{CC} pins must be on the same level.
4. The supply voltage with all V_{SS} pins must be on the same level.

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DC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, V_{SS} = 0V)

Parameter	Symbol	Min	Typ* ¹	Max	Unit	Test conditions
Input leakage current	I _{I_I}	—	—	2	μA	V _{in} = V _{SS} to V _{CC}
Output leakage current	I _{I_O}	—	—	2	μA	V _{in} = V _{SS} to V _{CC}
Operation power supply current	I _{CC}	—	—	115	mA	Min cycle CS = V _{IL} , I _{out} = 0 mA Other inputs = V _{IH} /V _{IL}
Standby power supply current	I _{SB}	—	—	40	mA	Min cycle CS = V _{IH} , Other inputs = V _{IH} /V _{IL}
	I _{SB1}	—	TBD	5	mA	f = 0 MHz V _{CC} ≥ CS ≥ V _{CC} - 0.2 V, (1) 0 V ≤ V _{in} ≤ 0.2 V or (2) V _{CC} ≥ V _{in} ≥ V _{CC} - 0.2 V
	—* ²	—	TBD* ²	1.0* ²		
Output voltage	V _{OL}	—	—	0.4	V	I _{OL} = 8 mA
	V _{OH}	2.4	—	—	V	I _{OH} = -4 mA

Notes: 1. Typical values are at V_{CC} = 3.3 V, Ta = +25°C and not guaranteed.
2. This characteristics is guaranteed only for L-version.

Capacitance (Ta = +25°C, f = 1.0 MHz)

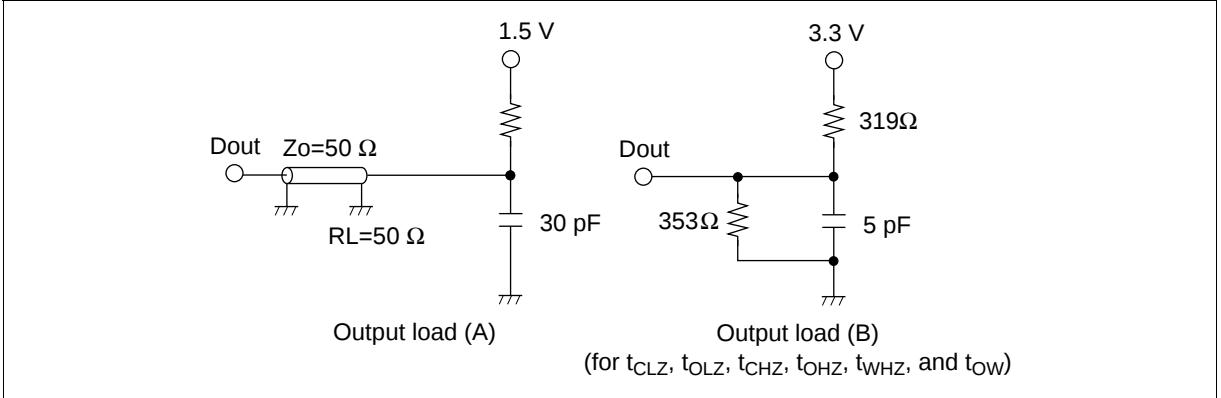
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance* ¹	C _{in}	—	—	6	pF	V _{in} = 0 V
Input/output capacitance* ¹	C _{I/O}	—	—	8	pF	V _{I/O} = 0 V

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, VCC = 3.3 V ± 0.3 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: 3.0 V/0.0 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures (Including scope and jig)



Read Cycle

		HM62W8511HC			
		-10			
Parameter	Symbol	Min	Max	Unit	Notes
Read cycle time	t _{RC}	10	—	ns	
Address access time	t _{AA}	—	10	ns	
Chip select access time	t _{ACS}	—	10	ns	
Output enable to outpput valid	t _{OE}	—	5	ns	
Output hold from address change	t _{OH}	3	—	ns	
Chip select to output in low-Z	t _{CLZ}	3	—	ns	1
Output enable to output in low-Z	t _{OLZ}	0	—	ns	1
Chip deselect to output in high-Z	t _{CHZ}	—	5	ns	1
Output disable to output in high-Z	t _{OHZ}	—	5	ns	1

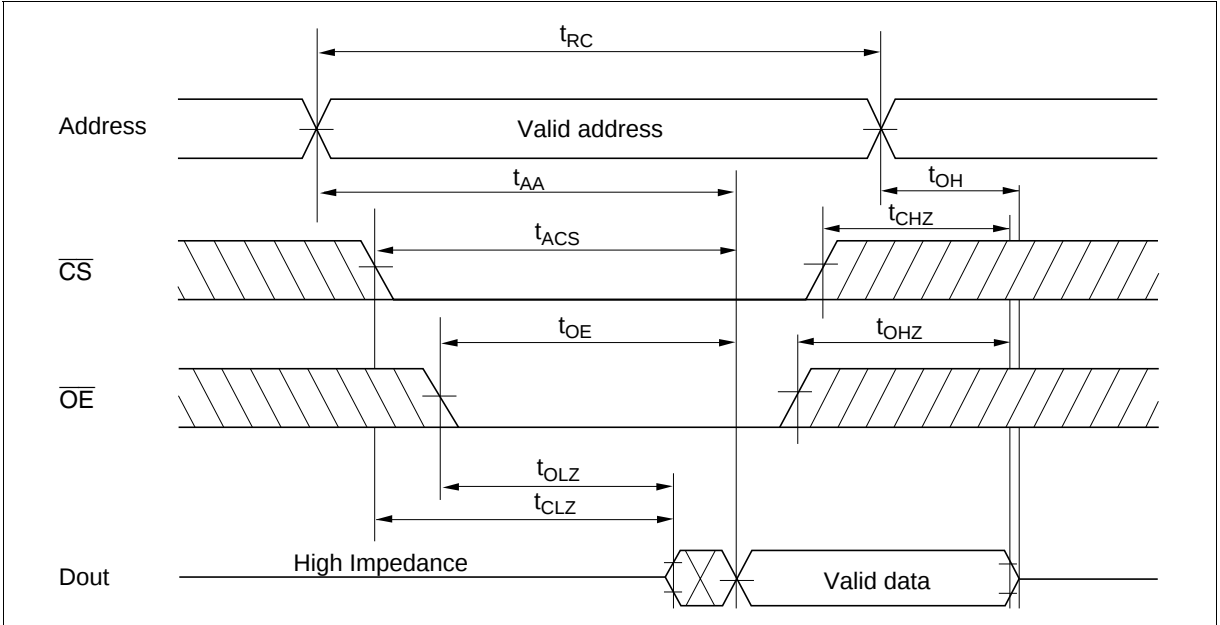
Write Cycle

		HM62W8511HC			
		-10			
Parameter	Symbol	Min	Max	Unit	Notes
Write cycle time	t _{WC}	10	—	ns	
Address valid to end of write	t _{AW}	7	—	ns	
Chip select to end of write	t _{CW}	7	—	ns	9
Write pulse width	t _{WP}	7	—	ns	8
Address setup time	t _{AS}	0	—	ns	6
Write recovery time	t _{WR}	0	—	ns	7
Data to write time overlap	t _{DW}	5	—	ns	
Data hold from write time	t _{DH}	0	—	ns	
Write disable to output in low-Z	t _{OW}	3	—	ns	1
Output disable to output in high-Z	t _{OHZ}	—	5	ns	1
Write enable to output in high-Z	t _{WHZ}	—	5	ns	1

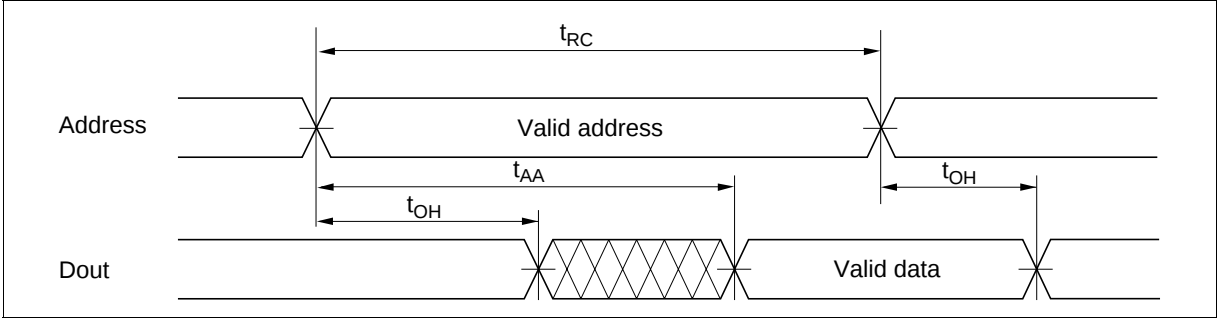
- Note:
1. Transition is measured ± 200 mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.
 2. Address should be valid prior to or coincident with $\overline{CS}$ transition low.
 3. $\overline{WE}$ and/or $\overline{CS}$ must be high during address transition time.
 4. if $\overline{CS}$ and $\overline{OE}$ are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.
 5. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, output remains a high impedance state.
 6. t_{AS} is measured from the latest address transition to the later of $\overline{CS}$ or $\overline{WE}$ going low.
 7. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the first address transition.
 8. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS}$ going low and $\overline{WE}$ going low. A write ends at the earliest transition among $\overline{CS}$ going high and $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
 9. t_{CW} is measured from the later of $\overline{CS}$ going low to the the end of write.

Timing Waveforms

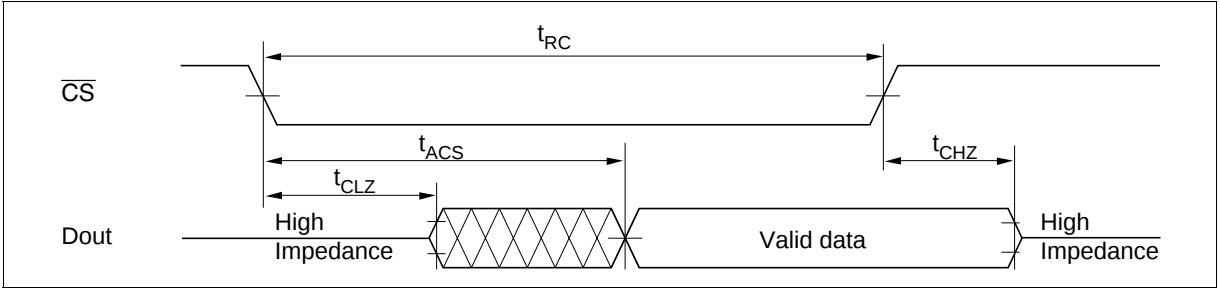
Read Timing Waveform (1) ($\overline{WE} = V_{IH}$)



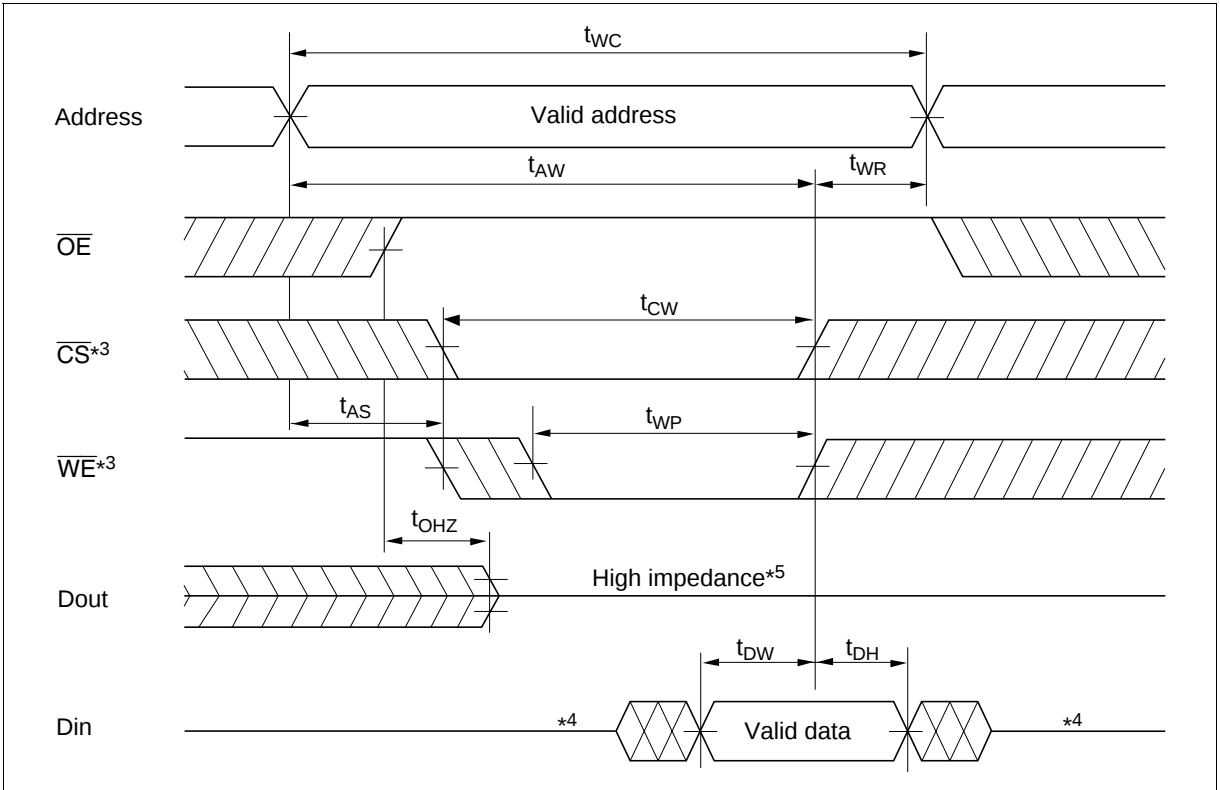
Read Timing Waveform (2) ($\overline{WE} = V_{IH}$, $\overline{CS} = V_{IL}$, $\overline{OE} = V_{IL}$)



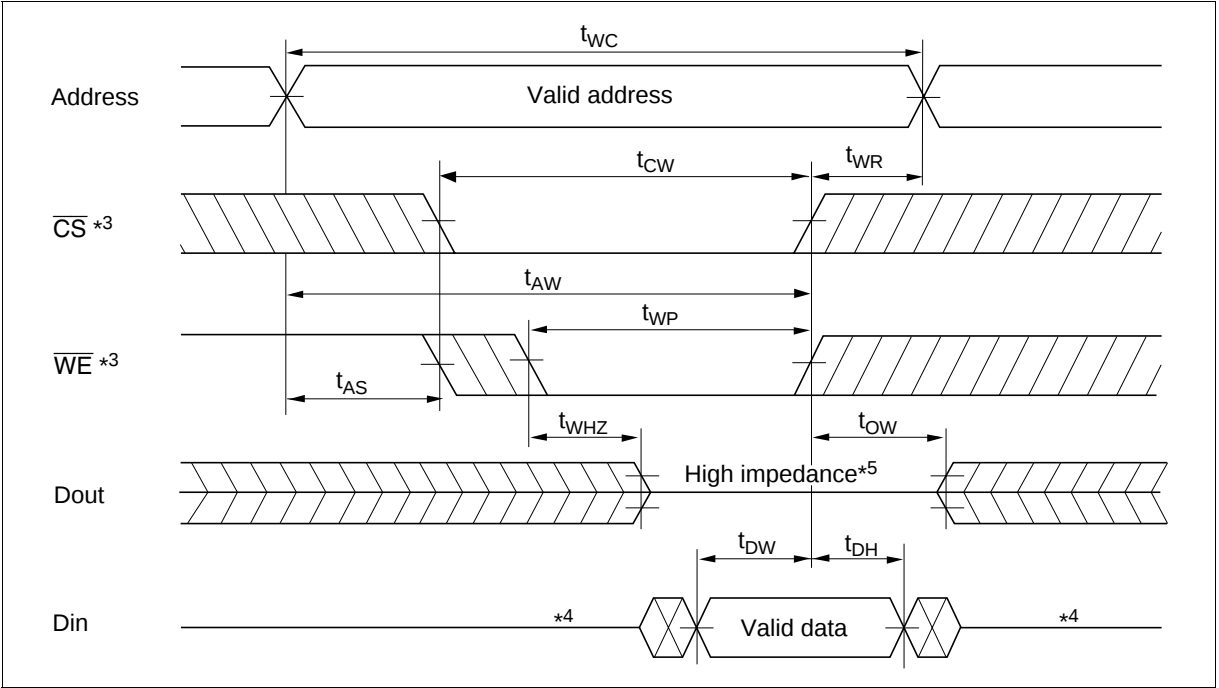
Read Timing Waveform (3) ($\overline{WE} = V_{IH}$, $\overline{CS} = V_{IL}$, $\overline{OE} = V_{IL}$)*2



Write Timing Waveform (1) ($\overline{WE}$ Controlled)



Write Timing Waveform (2) ($\overline{\text{CS}}$ Controlled)



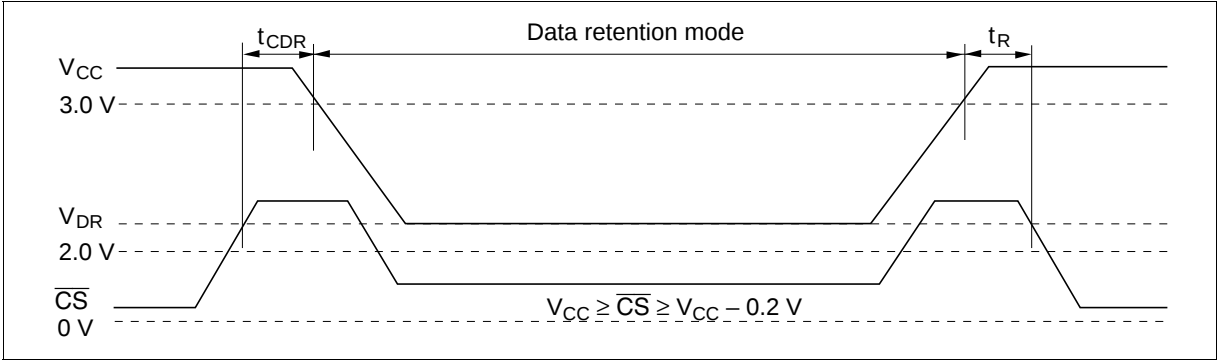
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions
V _{CC} for data retention	V _{DR}	2.0	—	—	V	V _{CC} ≥ $\overline{CS}$ ≥ V _{CC} − 0.2 V (1) 0 V ≤ Vin ≤ 0.2 V or (2) V _{CC} ≥ Vin ≥ V _{CC} − 0.2 V
Data retention current	I _{CCDR}	—	TBD	600	μA	V _{CC} = 3 V, V _{CC} ≥ $\overline{CS}$ ≥ V _{CC} − 0.2 V (1) 0 V ≤ Vin ≤ 0.2 V or (2) V _{CC} ≥ Vin ≥ V _{CC} − 0.2 V
Chip deselect to data retention time	t _{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t _R	5	—	—	ms	

Note: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C, and not guaranteed.

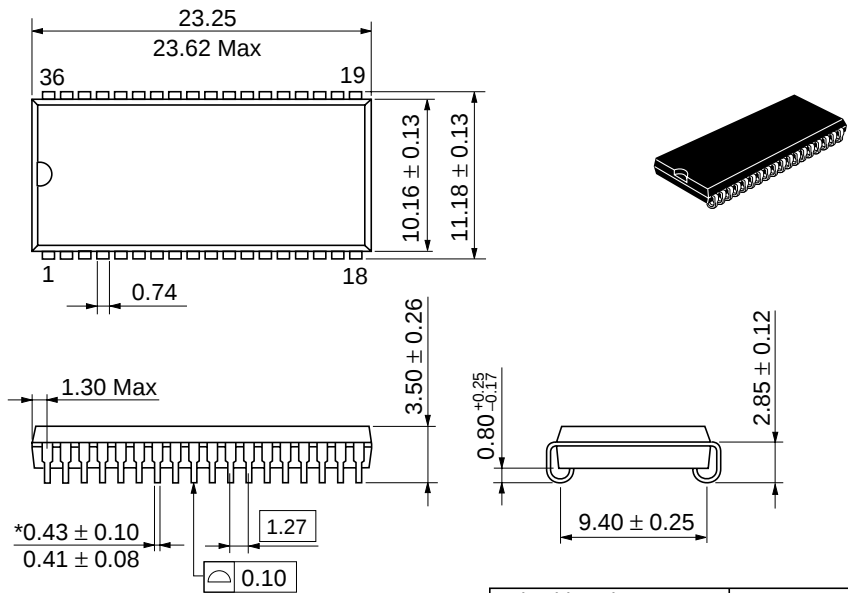
Low V_{CC} Data Retention Timing Waveform



Package Dimensions

HM62W8511HCJP/HCLJP Series (CP-36D)

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	CP-36D
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.4 g

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